

TA8270HQ

Max Power 43 W BTL × 4 ch High Efficiency Audio Power IC

The TA8270HQ is TOSHIBA original class KB (Keyed BTL) high efficiency audio amplifier for car audio applications.

The Class KB solutions is no need an external LPF for EMI rejection and then it is possible to design for limited small DIN size chassis.

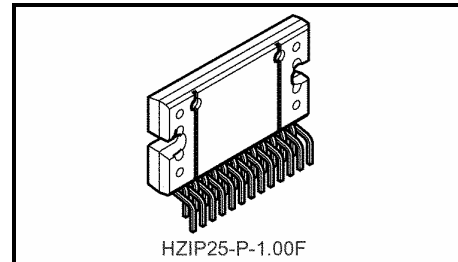
Conversely, the class D must need an external LPF.

Power dissipation of class KB is no more than a half of the class AB solutions.

Therefore, it is possible to design a smaller heatsink and keep lower internal temperature into the car audio set; internal cassette part, CD/MD part etc.

This IC can generate more high power and high quality sounds as it is included the pure complementary PNP and NPN transistor output stage.

Additionally, stand-by function, mute function, various kind of protector and diagnosis function included output offset voltage detection for car audio use are built-in.



Weight: 7.7 g (typ.)

Features

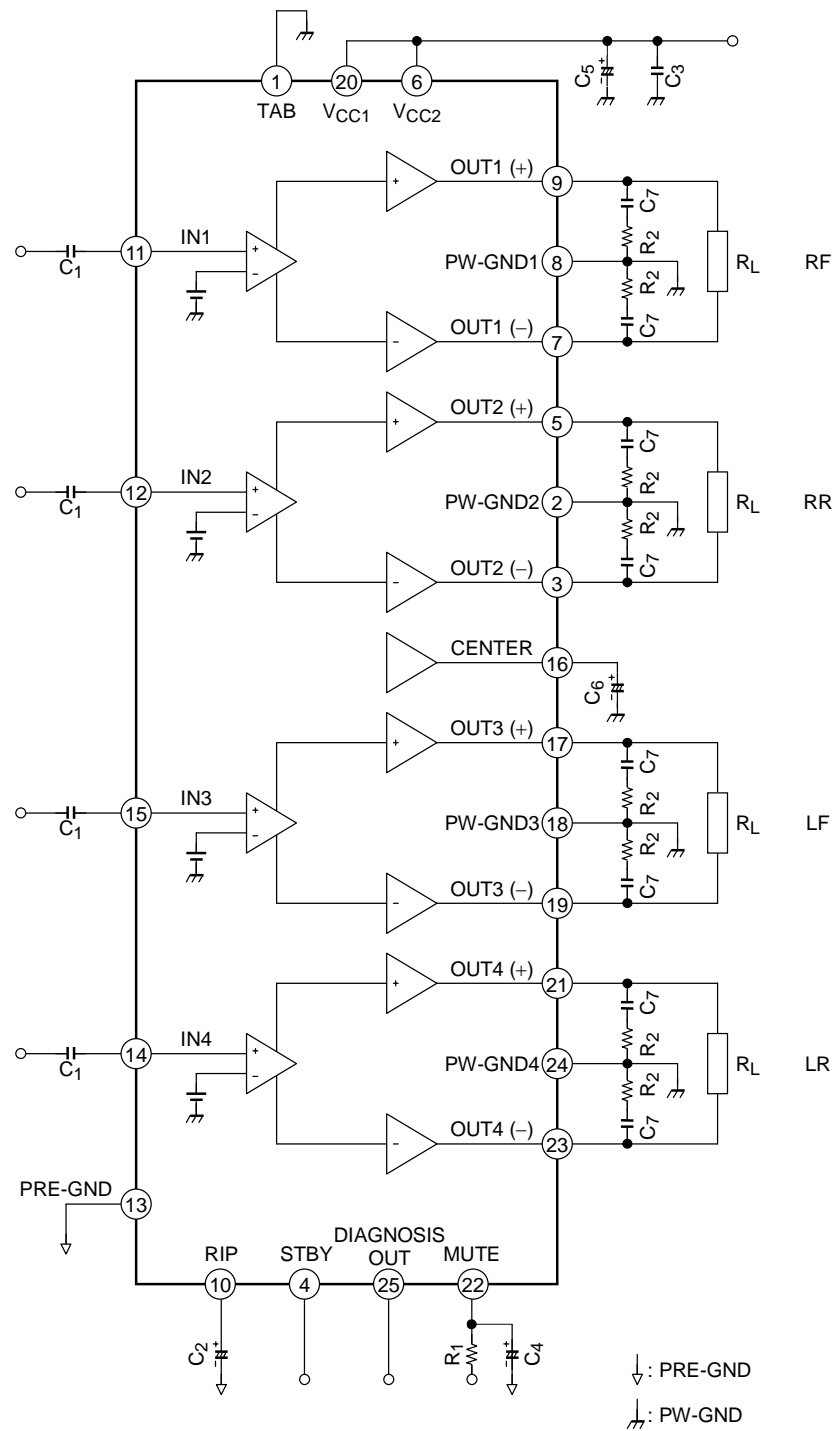
- High power: $P_{OUTMAX} (1) = 43 \text{ W (typ.)}$
 $(V_{CC} = 14.4 \text{ V, } f = 1 \text{ kHz, JEITA max, } R_L = 4 \Omega)$
 $: P_{OUTMAX} (2) = 40 \text{ W (typ.)}$
 $(V_{CC} = 13.7 \text{ V, } f = 1 \text{ kHz, JEITA max, } R_L = 4 \Omega)$
 $: P_{OUT} (1) = 28 \text{ W (typ.)}$
 $(V_{CC} = 14.4 \text{ V, } f = 1 \text{ kHz, THD} = 10\%, R_L = 4 \Omega)$
 $: P_{OUT} (2) = 24 \text{ W (typ.)}$
 $(V_{CC} = 13.2 \text{ V, } f = 1 \text{ kHz, THD} = 10\%, R_L = 4 \Omega)$
- Built-in diagnosis circuit (pin 25)
- Low distortion ratio: $\text{THD} = 0.04\% \text{ (typ.)}$
 $(V_{CC} = 13.2 \text{ V, } f = 1 \text{ kHz, } P_{OUT} = 2 \text{ W, } R_L = 4 \Omega)$
- Low noise: $V_{NO} = 0.13 \text{ mV}_{rms} \text{ (typ.)}$
 $(V_{CC} = 13.2 \text{ V, } R_g = 0 \Omega, G_V = 26\text{dB, BW} = 20 \text{ Hz} \sim 20 \text{ kHz})$
- Built-in stand-by switch (pin 4)
- Built-in muting function (pin 22)
- Built-in various protection circuit
 $: \text{Thermal shut down, over voltage, out to GND, out to VCC, out to out short}$
- Operating supply voltage: $V_{CC} (\text{opr}) = 9 \sim 16 \text{ V}$

Note 1: Install the product correctly. Otherwise, it may result in break down, damage and/or degradation to the product or equipment.

Note 2: These protection functions are intended to avoid some output short circuits or other abnormal conditions temporarily. These protect functions do not warrant to prevent the IC from being damaged.

- In case of the product would be operated with exceeded guaranteed operating ranges, these protection features may not operate and some output short circuits may result in the IC being damaged.

Block Diagram



Note3: Some of the functional blocks, circuits, or constants in the block diagram may be omitted or simplified for explanatory purpose.

Caution and Application Method

(Description is made only on the single channel.)

1. Voltage Gain Adjustment

This IC has no NF (negative feedback) terminals. Therefore, the voltage gain can't adjusted, but it makes the device a space and total costs saver.

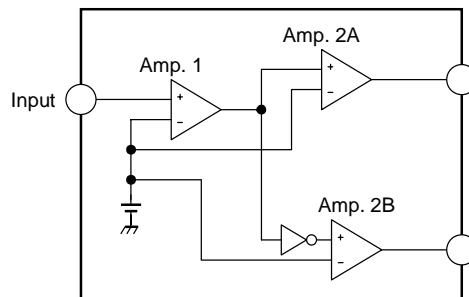


Figure 1 Block Diagram

The voltage gain of Amp.1: $GV_1 = 0\text{dB}$

The voltage gain of Amp.2A, B: $GV_2 = 20\text{dB}$

The voltage gain of BLT Connection: $GV(\text{BTL}) = 6\text{dB}$

Therefore, the total voltage gain is decided by expression below.

$$GV = GV_1 + GV_2 + GV(\text{BTL}) = 0 + 20 + 6 = 26\text{dB}$$

2. Stand-by SW Function (pin 4)

By means of controlling pin 4 (stand-by terminal) to high and low, the power supply can be set to ON and OFF. The threshold voltage of pin 4 is set at about $3V_{BE}$ (typ.), and the power supply current is about $2\mu\text{A}$ (typ.) at the stand-by state.

Control Voltage of pin 4: V_{SB}

Stand-by	Power	V_{SB} (V)
ON	OFF	0~1.5
OFF	ON	3~ V_{CC}

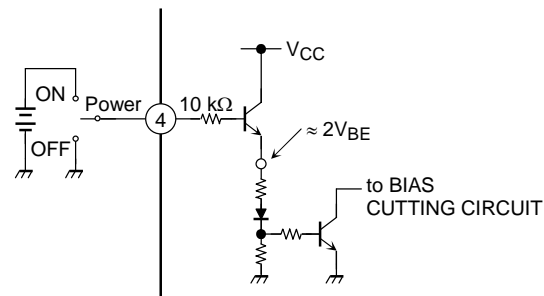


Figure 2 With pin 4 set to High, Power is turned ON

Adjustage of Stand-by SW

- (1) Since V_{CC} can directly be controlled to ON or OFF by the microcomputer, the switching relay can be omitted.
- (2) Since the control current is microscopic, the switching relay of small current capacity is satisfactory for switching

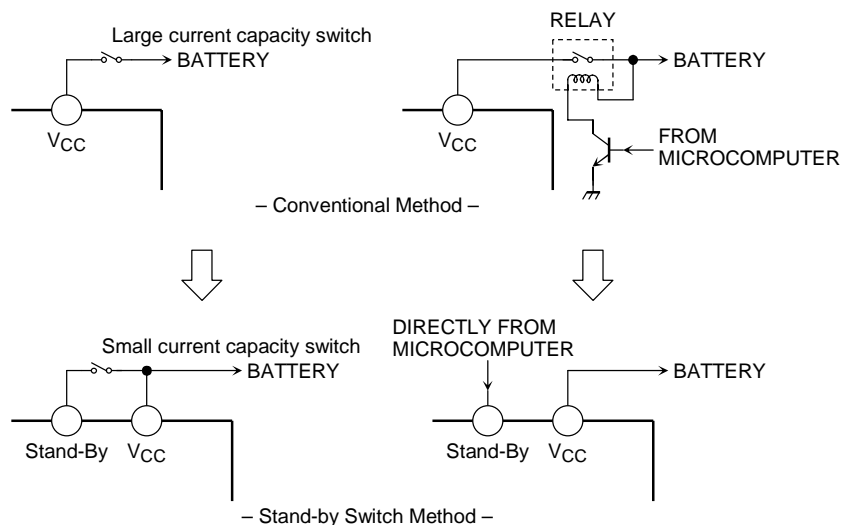


Figure 3

3. Muting Function (pin 22)

By means of controlling pin 22 less than 0.5 V, it can make the audio muting condition.

The muting time constant is decided by R_1 and C_4 and these parts is related the pop noise at power ON/OFF.

The series resistance; R_1 must be set up less than 10 k Ω to get enough muting attenuation.

The muting function have to be controlled by a transistor, FET and μ -COM port which has $I_{MUTE} > 250 \mu A$ ability.

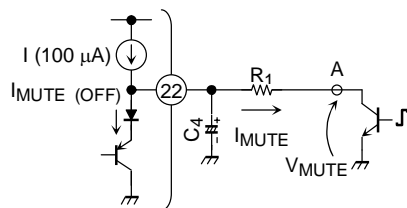
Pin 22 terminal voltage has the temperature characteristics of 4.6 V (low temperature) to 3.2 V (high temperature).

Therefore, it is need to design with attention as using the microcontroller of which operating voltage is less than 5 V.

Terminal 22 may not be pulled up and shall be controlled by OPEN/LOW.

When it is obliged to do, it must be pulled up via diode, because it has to defend flowing reverse current to internal circuit of pin 22.

<Recommended Application>



<Application for pulled up>

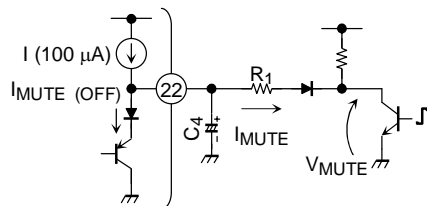
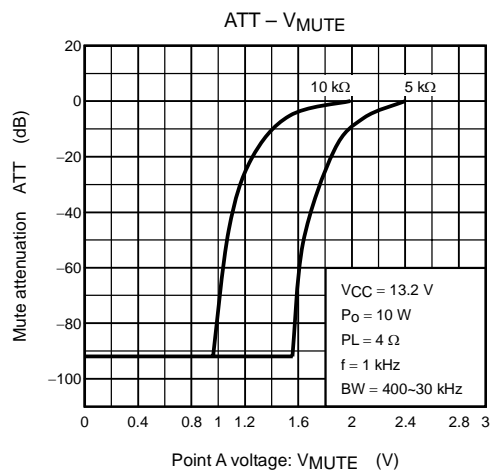


Figure 4 Muting Function

Figure 5 Mute Attenuation – V_{MUTE} (V)

4. Center Amp Pin: Center (pin 16)

Output from the center amp, which determines the reference voltage for output in the IC, is connected to this pin.

Connecting a capacitor to the pin rejects the ripple component, reducing the distortion ratio of the audio output.

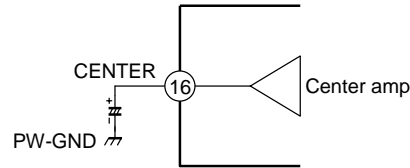


Figure 6 CENTER

5. Diagnosis Output (pin 25)

This diagnosis output terminal of pin 25 has open collector output structure on chip as shown in Figure 7. In case diagnosis circuit that detect unusual case is operated, NPN transistor. (Q1) or (Q2) is turned on. It is possible to protect all the system of apparatus as well as power IC protection.

In case of being unused this function, use this IC as open-connection on pin 25.

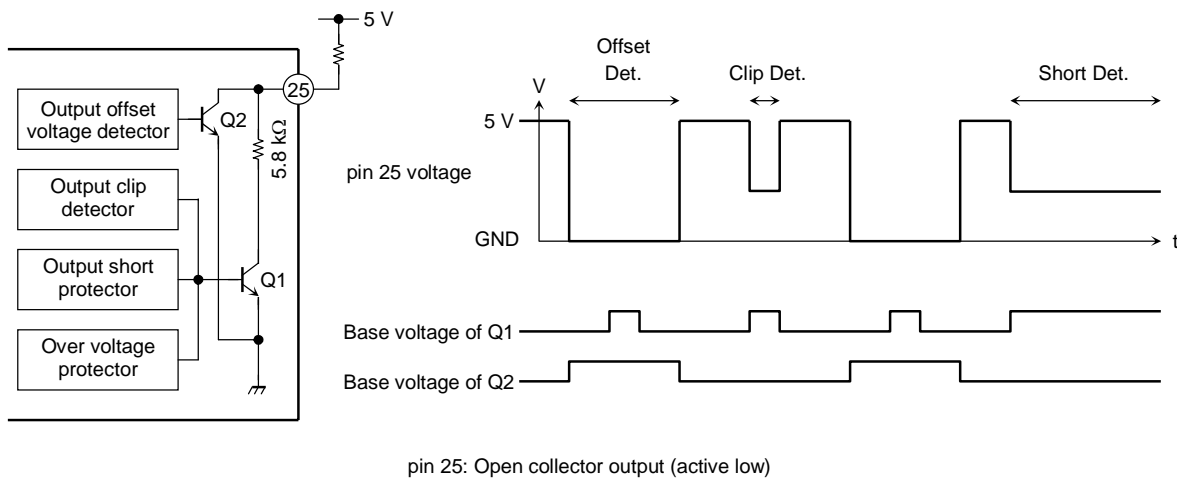


Figure 7 Self Diagnosis Output

5.1 In Case of Shorting Output to V_{CC} /GND or Over Voltage Power Supplied

NPN transistor. (Q1) is turned on.

Threshold of over voltage protection: $V_{CC} = 22 \text{ V}$ (typ.)

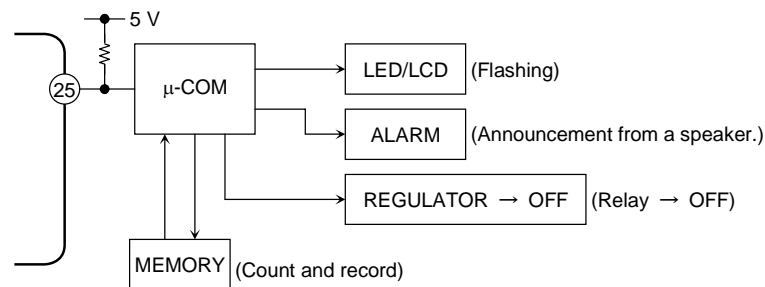


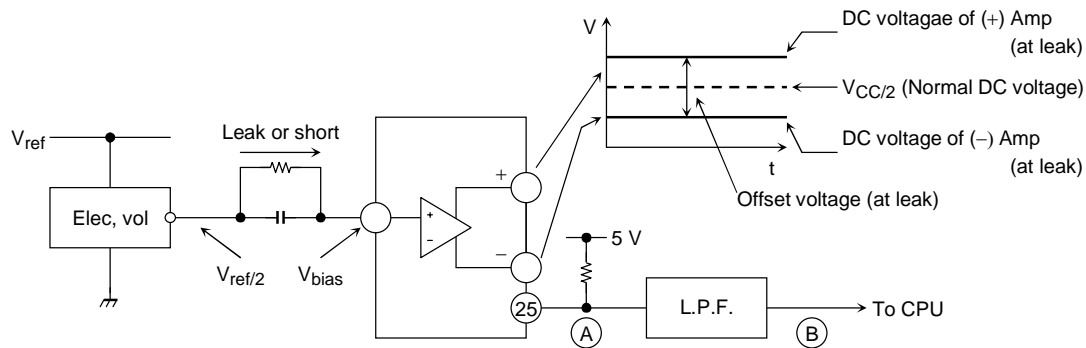
Figure 8 Application 1

5.2 In Case of Shorting Output to Output

NPN transistor. (Q1) is turned on and off in response to the input signal voltage.

5.3 In Case of Appearing output Offset Voltage by Generation a Large Leakage Current on the Input Capacitor etc.

NPN transistor. (Q2) is turned on while the inverted output voltage level become less than the threshold level of output offset voltage detector.



Note 4: It is possible to detect the abnormal output offset which is appeared by the large leakage of the input capacitor at $V_{ref}/2 > V_{bias}$ (about 1.4 V)

Figure 9 Application and Detection Mechanism

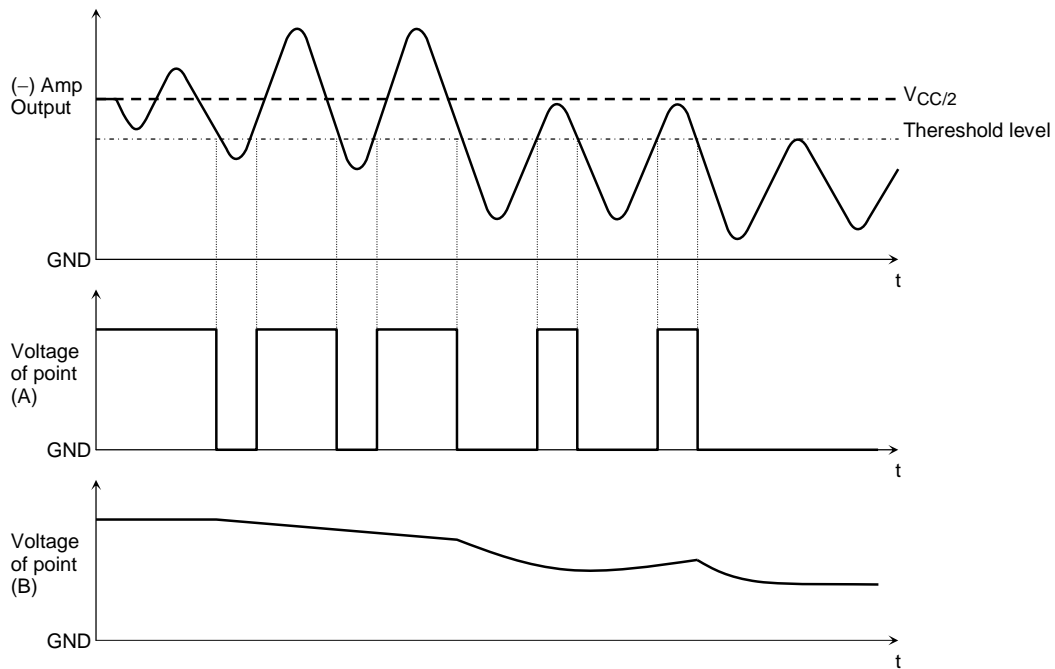


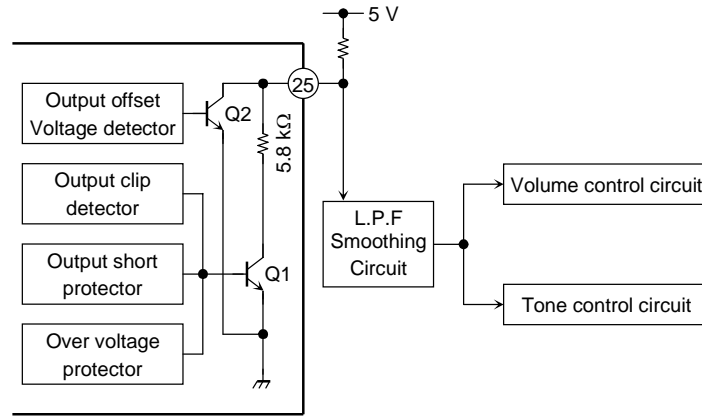
Figure 10 Wave Form

6. Output Clip Detection Function (pin 25)

The output clip detection terminal of pin 25 has the open collector output structure on chip as shown in Figure 11. In case that the output waveform is clipping, the clip detection circuit is operated and NPN transistor is turned on.

It is possible to improve the audio quality with controlling the volume, tone control circuit through L.P.F. smoothing circuit as shown in Figure 11.

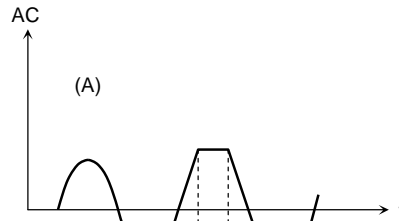
In case of being unused this function, use this IC as open connection on pin 25.



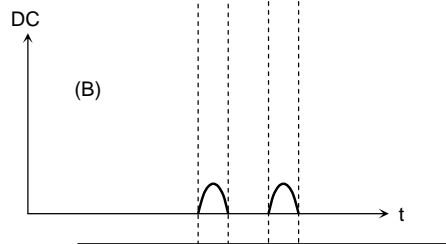
Pin25: Open collector output (active low)

Figure 11

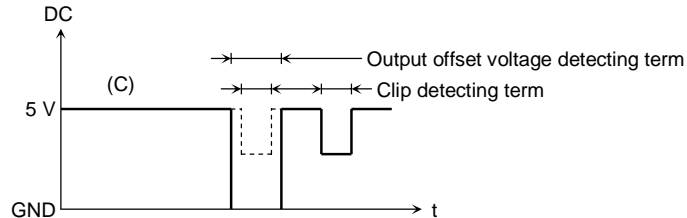
(A) Output (AC wave form)



(B) Clip Detector Circuit (internal)



(C) Clip Detector Terminal (pin 25)



Note: Actually, the waveform is solid line because the output offset voltage detection, which is a kind of the self diagnosis, has priority.

Figure 12 Clip Detection

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Peak supply voltage (0.2 s)	V _{CC} (surge)	50	V
DC supply voltage	V _{CC} (DC)	25	V
Operation supply voltage	V _{CC} (opr)	16	V
Output current (peak)	I _O (peak)	9	A
Power dissipation	P _D (Note5)	125	W
Operation temperature	T _{opr}	-40~85	°C
Storage temperature	T _{stg}	-55~150	°C

Note 5: Package thermal resistance $\theta_{j-T} = 1^{\circ}\text{C/W}$ (typ.)
(Ta = 25°C, with infinite heat sink)

The absolute maximum ratings of a semiconductor device are a set of specified parameter values, which must not be exceeded during operation, even for an instant. If any of these rating would be exceeded during operation, the device electrical characteristics may be irreparably altered and the reliability and lifetime of the device can no longer be guaranteed. Moreover, these operations with exceeded ratings may cause break down, damage and/or degradation to any other equipment. Applications using the device should be designed such that each absolute maximum rating will never be exceeded in any operating conditions. Before using, creating and/or producing designs, refer to and comply with the precautions and conditions set forth in this documents.

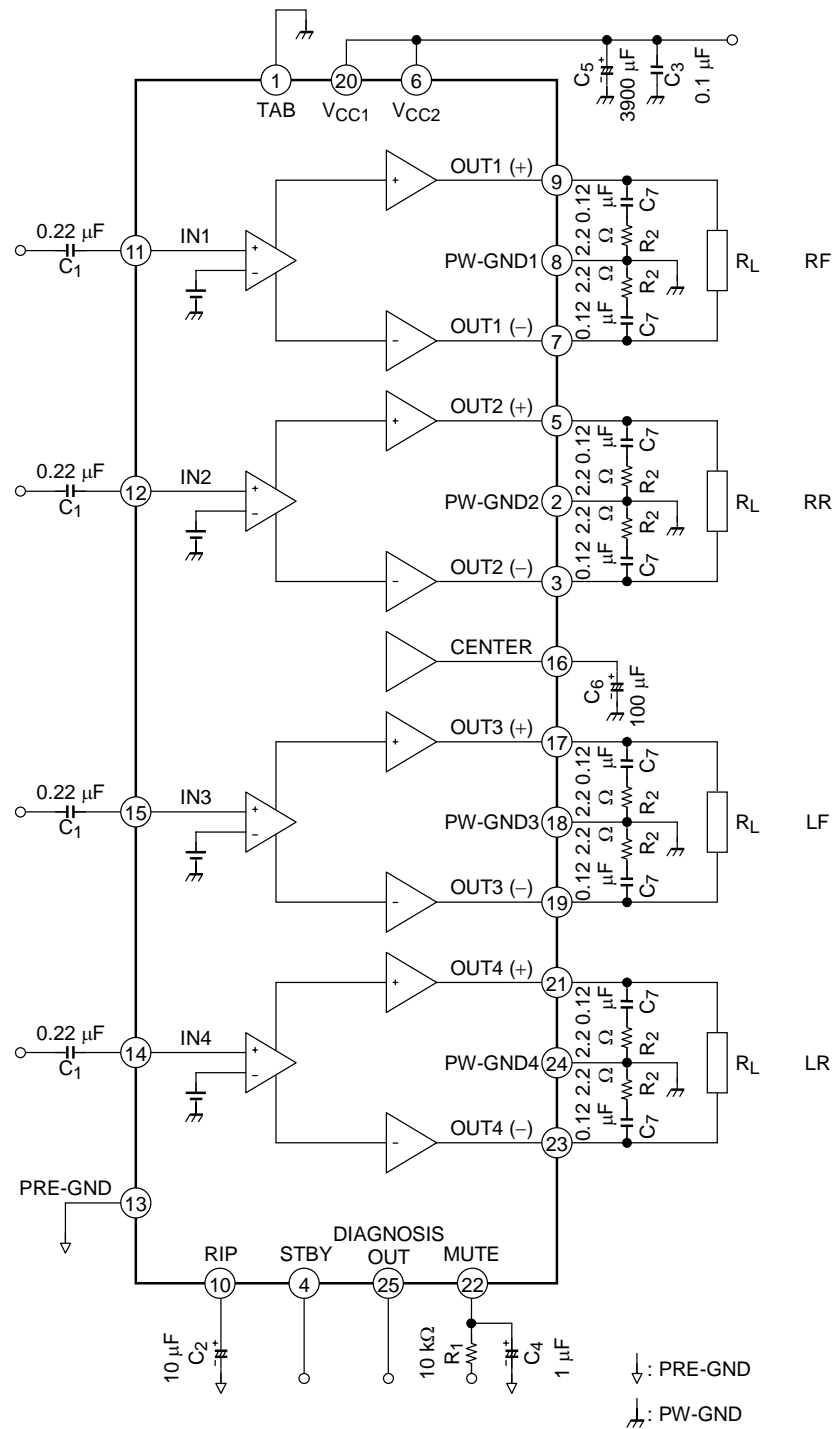
Electrical Characteristics

(unless otherwise specified, V_{CC} = 13.2 V, f = 1 kHz, R_L = 4 Ω, Ta = 25°C)

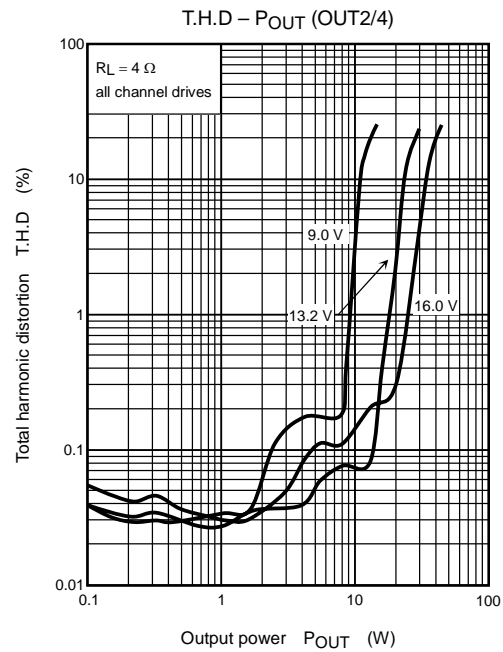
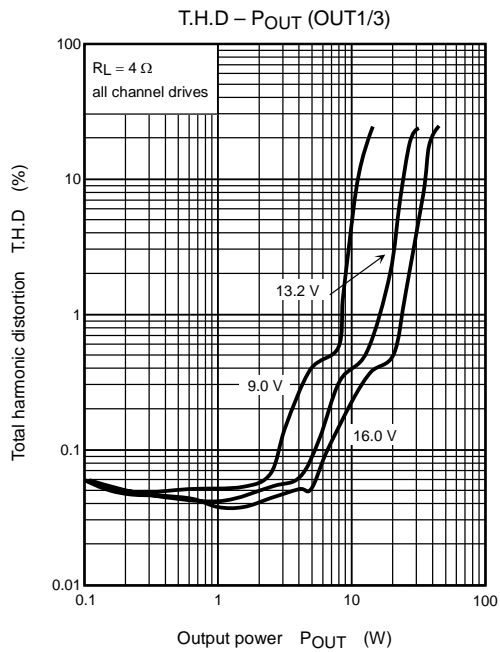
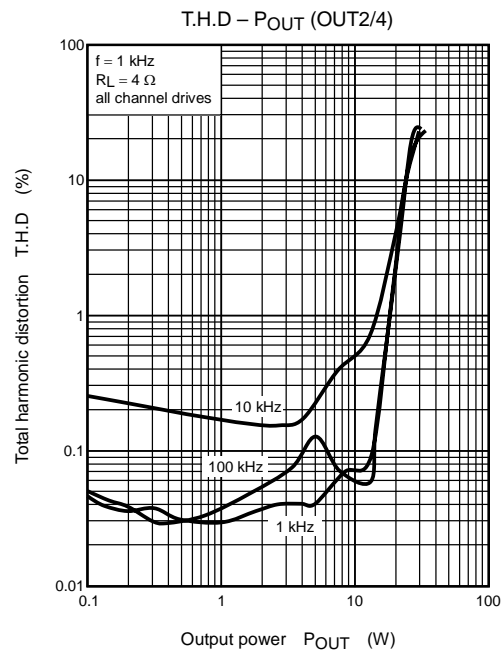
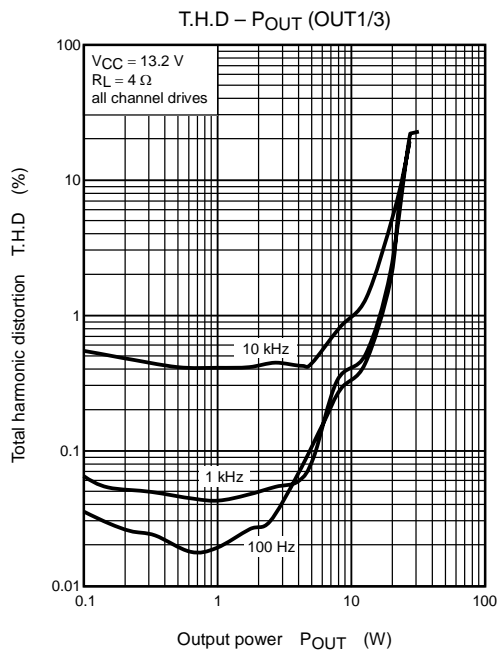
Characteristics	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Quiescent current	I _{CCQ}	—	V _{IN} = 0	—	200	400	mA
Output power	P _{OUT} MAX (1)	—	V _{CC} = 14.4 V, max Power	—	43	—	W
	P _{OUT} MAX (2)	—	V _{CC} = 13.7 V, max Power	—	40	—	
	P _{OUT} (1)	—	V _{CC} = 14.4 V, THD = 10%	—	28	—	
	P _{OUT} (2)	—	THD = 10%	22	24	—	
Total harmonic distortion	THD	—	P _{OUT} = 2 W	—	0.04	0.2	%
Voltage gain	G _V	—	V _{OUT} = 0.775 V _{rms} (0dBm)	24	26	28	dB
Voltage gain ratio	ΔG _V	—	V _{OUT} = 0.775 V _{rms} (0dBm)	-1.0	0	1.0	
Output noise voltage	V _{NO} (1)	—	R _g = 0 Ω, DIN45405	—	0.15	—	mV _{rms}
	V _{NO} (2)	—	R _g = 0 Ω, BW = 20 Hz~20 kHz	—	0.13	0.35	
Ripple rejection ratio	R.R.	—	f _{rip} = 100 Hz, R _g = 620 Ω V _{rip} = 0.775 V _{rms} (0dBm)	40	50	—	dB
Cross talk	C.T.	—	R _g = 620 Ω V _{OUT} = 0.775 V _{rms} (0dBm)	—	65	—	dB
Output offset voltage	V _{OFFSET}	—	—	-150	0	150	mV
Input resistance	R _{IN}	—	—	—	90	—	kΩ
Stand-by current	I _{SB}	—	Stand-by condition	—	2	10	μA
Stand-by control voltage	V _{SB} H	—	Power: ON	3.0	—	V _{CC}	V
	V _{SB} L	—	Power: OFF	0	—	1.5	
Mute control voltage (Note 6)	V _M H	—	Mute: OFF	Open			—
	V _M L	—	Mute: ON, R ₁ = 10 kΩ	0	—	0.5	V
Mute attenuation	ATT M	—	Mute: ON, V _{OUT} = 7.75 V _{rms} (20dBm) at Mute: OFF.	80	90	—	dB

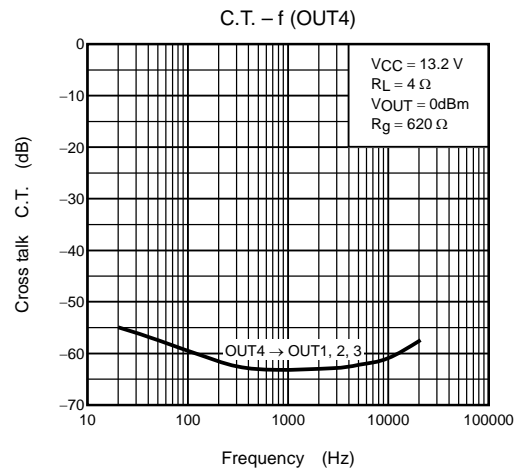
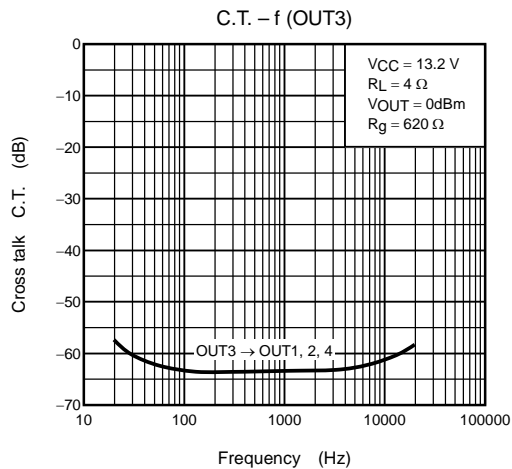
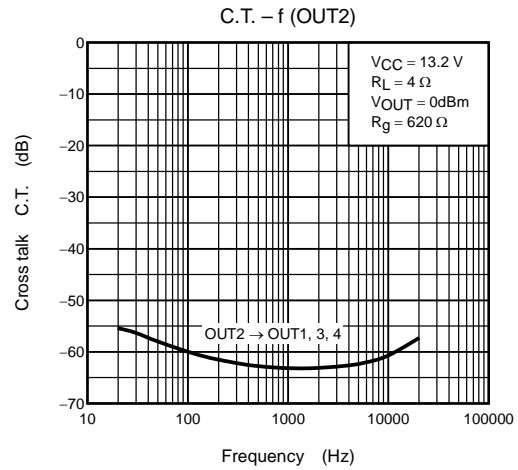
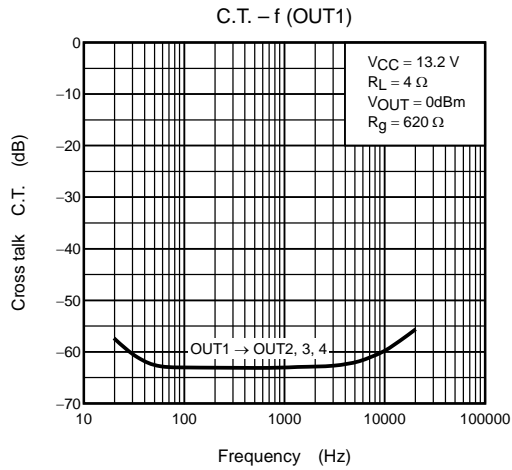
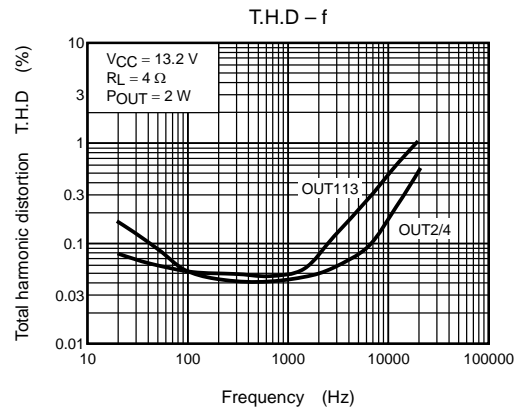
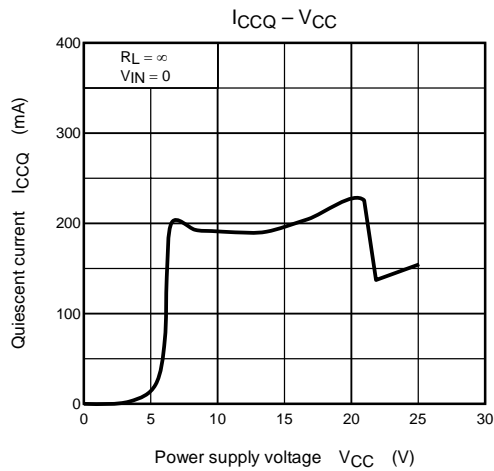
Note 6: Muting function have to be controlled by open and low logic, which logic is a transistor, FET and μ-COM port of I_{MUTE} > 250 μA ability. This means than the mute control terminal : pin 22 must not be pulled-up.

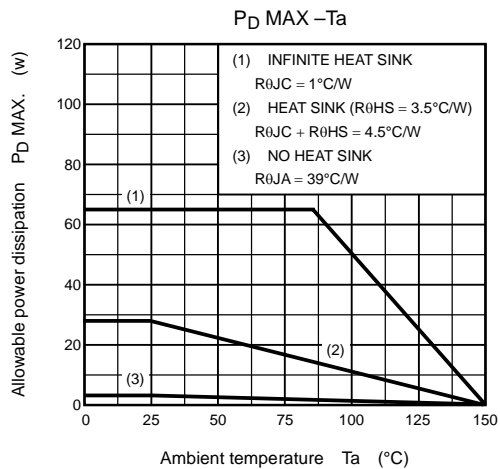
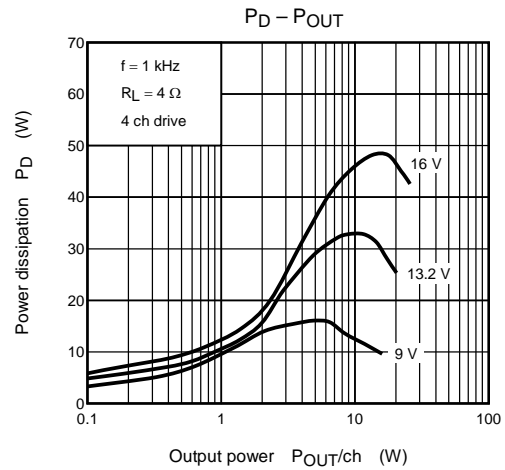
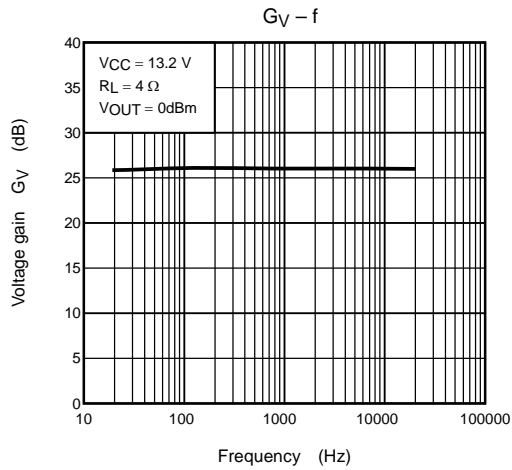
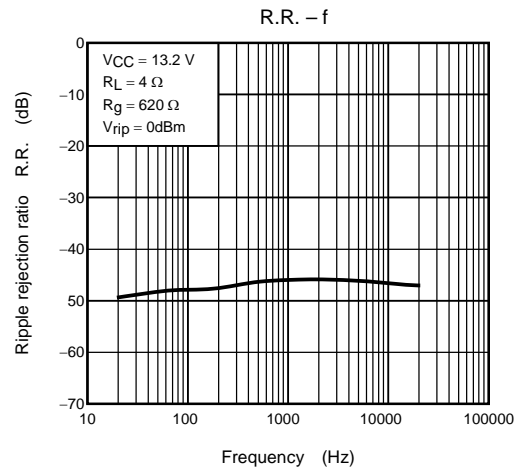
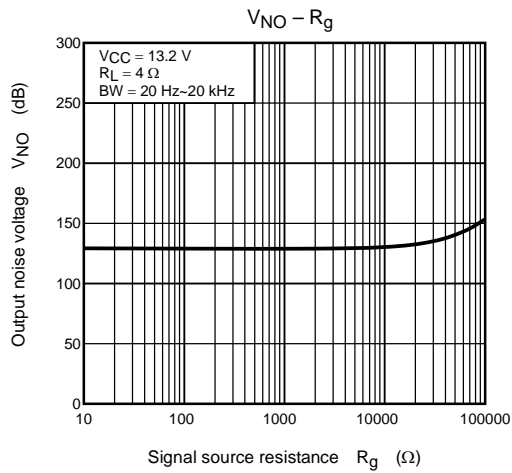
Test Circuit



Components in the test circuits are only used to obtain and confirm the device characteristics.
These components and circuits do not warrant to prevent the application equipment from malfunction or failure.



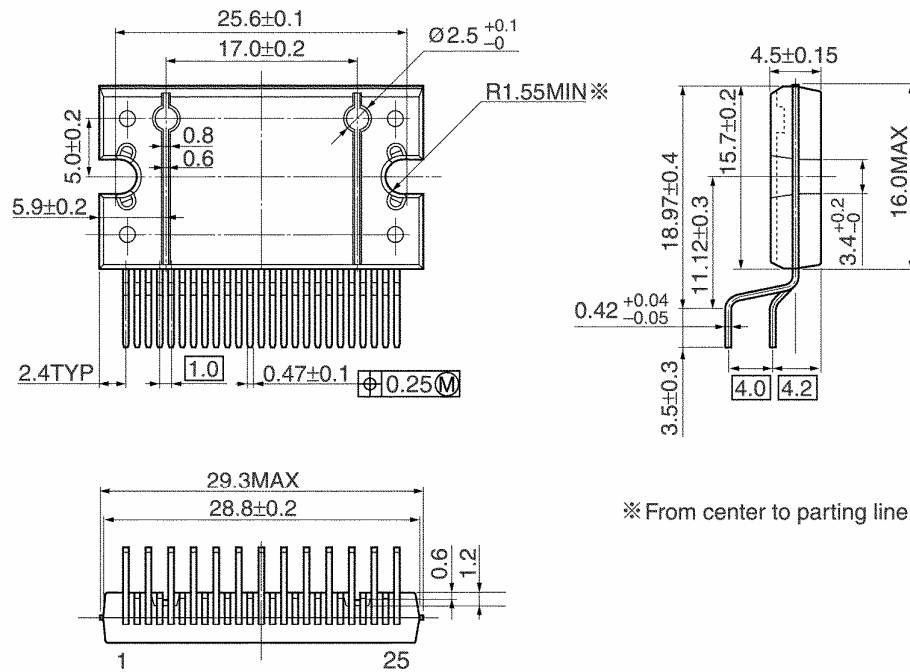




Package Dimensions

HZIP25-P-1.00F

Unit: mm



※ From center to parting line.

Weight: 7.7 g (typ.)

- Use an appropriate power supply fuse to ensure that a large current does not continuously flow in case of over current and/or IC failure. The IC will fully break down when used under conditions that exceed its absolute maximum ratings, when the wiring is routed improperly or when an abnormal pulse noise occurs from the wiring or load, causing a large current to continuously flow and the breakdown can lead smoke or ignition. To minimize the effects of the flow of a large current in case of breakdown, appropriate settings, such as fuse capacity, fusing time and insertion circuit location, are required.
- If your design includes an inductive load such as a motor coil, incorporate a protection circuit into the design to prevent device malfunction or breakdown caused by the current resulting from the inrush current at power ON or the negative current resulting from the back electromotive force at power OFF. For details on how to connect a protection circuit such as a current limiting resistor or back electromotive force adsorption diode, refer to individual IC datasheets or the IC databook. IC breakdown may cause injury, smoke or ignition.
- Use a stable power supply with ICs with built-in protection functions. If the power supply is unstable, the protection function may not operate, causing IC breakdown. IC breakdown may cause injury, smoke or ignition.
- Carefully select external components (such as inputs and negative feedback capacitors) and load components (such as speakers), for example, power amp and regulator. If there is a large amount of leakage current such as input or negative feedback condenser, the IC output DC voltage will increase. If this output voltage is connected to a speaker with low input withstand voltage, overcurrent or IC failure can cause smoke or ignition. (The over current can cause smoke or ignition from the IC itself.) In particular, please pay attention when using a Bridge Tied Load (BTL) connection type IC that inputs output DC voltage to a speaker directly.
- Over current Protection Circuit
Over current protection circuits (referred to as current limiter circuits) do not necessarily protect ICs under all circumstances. If the Over current protection circuits operate against the over current, clear the over current status immediately. Depending on the method of use and usage conditions, such as exceeding absolute maximum ratings can cause the over current protection circuit to not operate properly or IC breakdown before operation. In addition, depending on the method of use and usage conditions, if over current continues to flow for a long time after operation, the IC may generate heat resulting in breakdown.
- Thermal Shutdown Circuit
Thermal shutdown circuits do not necessarily protect ICs under all circumstances. If the Thermal shutdown circuits operate against the over temperature, clear the heat generation status immediately. Depending on the method of use and usage conditions, such as exceeding absolute maximum ratings can cause the thermal shutdown circuit to not operate properly or IC breakdown before operation.
- Heat Radiation Design
When using an IC with large current flow such as power amp, regulator or driver, please design the device so that heat is appropriately radiated, not to exceed the specified junction temperature (T_j) at any time and condition. These ICs generate heat even during normal use. An inadequate IC heat radiation design can lead to decrease in IC life, deterioration of IC characteristics or IC breakdown. In addition, please design the device taking into consideration the effect of IC heat radiation with peripheral components.
- Installation to Heat Sink
Please install the power IC to the heat sink not to apply excessive mechanical stress to the IC. Excessive mechanical stress can lead to package cracks, resulting in a reduction in reliability or breakdown of internal IC chip. In addition, depending on the IC, the use of silicon rubber may be prohibited. Check whether the use of silicon rubber is prohibited for the IC you intend to use, or not. For details of power IC heat radiation design and heat sink installation, refer to individual technical datasheets or IC databooks.

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060116EBF

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The product is often the final stage (the external output stage) of a circuit. Substandard performance or malfunction of the destination device to which the circuit supplies output may cause damage to the circuit or to the product. 030619_R

About solderability, following conditions were confirmed

- Solderability
 - (1) Use of Sn-37Pb solder Bath
 - solder bath temperature = 230°C
 - dipping time = 5 seconds
 - the number of times = once
 - use of R-type flux
 - (2) Use of Sn-3.0Ag-0.5Cu solder Bath
 - solder bath temperature = 245°C
 - dipping time = 5 seconds
 - the number of times = once
 - use of R-type flux